ABSTRACT OF THE DISCLOSURE

A METHOD OF PRODUCING A THIN LAYER OF SEMICONDUCTOR MATERIAL

The invention relates to a method of producing a thin layer of semiconductor material including :

- a step of implanting ions through a flat face (2) of a semiconductor wafer in order to create a layer of microcavities, the ion dose being within a specific range in order to avoid the formation of blisters on the flat face,
- a thermal treatment step in order to achieve coalescence of the microcavities
- possibly, a step of creating at least one electronic component (5) in the thin layer (6),
- a separation step of separating the thin layer (6) from the rest (7) of the wafer.

Figure 4.